

WHAT IS CLAIMED IS:

1. A method of processing a substrate, comprising the steps of:
transferring the substrate from an ambient environment into a clean environment,
heating the substrate to at least a first temperature within the clean environment,
maintaining the substrate at no less than the first temperature within the clean
5 environment,
selectively transferring the substrate within the clean environment to more than
one processing chambers,
processing the substrate in the more than one processing chambers, and
transferring the substrate from the clean environment into the ambient
10 environment.
2. The method of claim 1 wherein the step of maintaining the substrate at no less
than the first temperature within the clean environment comprises heating all of
the clean environment to at least the first temperature.
3. The method of claim 1 wherein the step of maintaining the substrate at no less
than the first temperature within the clean environment comprises transferring and
processing the substrate quickly through the more than one processing chambers
within the clean environment so that the substrate does not have time to cool
5 below the first temperature.
4. The method of claim 1 wherein the step of maintaining the substrate at no less
than the first temperature within the clean environment comprises heating the
substrate to at least the first temperature within each of the more than one
processing chambers, and transferring the substrate quickly between the more
5 than one processing chambers within the clean environment so that the substrate
does not have time to cool below the first temperature between the more than one
processing chambers.
5. The method of claim 1 wherein the first temperature is at least about 150
centigrade.

6. The method of claim 1 wherein the first temperature is no more than about 350 centigrade.
7. The method of claim 1 further comprising the steps of reducing a pressure within the clean environment to a base pressure of between about 10^{-7} torr and about 10^{-9} torr.
8. The method of claim 1 wherein the step of processing the substrate in the more than one processing chambers further comprises selectively adjusting a pressure within the more than one processing chambers while processing the substrate in the more than one processing chambers.
9. The method of claim 1 wherein the step of processing the substrate in the more than one processing chambers further comprises:
heating the substrate under a vacuum in a degassing chamber,
etching the substrate in an etch chamber, and
depositing a layer onto the substrate in a deposition chamber.
10. The method of claim 1 wherein the step of processing the substrate in the more than one processing chambers further comprises:
heating the substrate under a vacuum in a degassing chamber,
etching the substrate in an etch chamber,
depositing a layer of titanium in a first deposition chamber, and
depositing a layer of titanium nitride in a second deposition chamber.
11. A method of processing a substrate, comprising the steps of:
transferring the substrate from an ambient environment into a clean environment,
heating the substrate to at least a first temperature within the clean environment,
maintaining the substrate at no less than the first temperature within the clean environment by heating all of the clean environment to at least the first temperature,
selectively transferring the substrate within the clean environment to more than one processing chambers,

- 10 processing the substrate in the more than one processing chambers, and
transferring the substrate from the clean environment into the ambient
environment.
12. The method of claim 11 wherein the first temperature is between about 150
centigrade and about 350 centigrade.
13. The method of claim 11 further comprising the steps of reducing a pressure within
the clean environment to a base pressure of between about 10^{-7} torr and about 10^{-9}
torr.
14. The method of claim 11 wherein the step of processing the substrate in the more
than one processing chambers further comprises:
heating the substrate under a vacuum in a degassing chamber,
etching the substrate in an etch chamber, and
5 depositing a layer onto the substrate in a deposition chamber.
15. The method of claim 11 wherein the step of processing the substrate in the more
than one processing chambers further comprises:
heating the substrate under a vacuum in a degassing chamber,
etching the substrate in an etch chamber,
depositing a layer of titanium in a first deposition chamber, and
depositing a layer of titanium nitride in a second deposition chamber.
16. A method of processing a substrate, comprising the steps of:
transferring the substrate from an ambient environment into a clean environment,
heating the substrate to at least a first temperature within the clean environment,
selectively transferring the substrate within the clean environment to more than
5 one processing chambers,
processing the substrate in the more than one processing chambers,
maintaining the substrate at no less than the first temperature within the clean
environment by transferring and processing the substrate quickly through
the more than one processing chambers within the clean environment so

10 that the substrate does not have time to cool below the first temperature,
 and
 transferring the substrate from the clean environment into the ambient
 environment.

17. The method of claim 16 wherein the first temperature is between about 150
 centigrade and about 350 centigrade.

18. The method of claim 16 further comprising the steps of reducing a pressure within
 the clean environment to a base pressure of between about 10^{-7} torr and about 10^{-9}
 torr.

19. The method of claim 16 wherein the step of processing the substrate in the more
 than one processing chambers further comprises selectively adjusting a pressure
 within the more than one processing chambers while processing the substrate in
 the more than one processing chambers.

20. The method of claim 16 wherein the step of processing the substrate in the more
 than one processing chambers further comprises:

 heating the substrate under a vacuum in a degassing chamber,

 etching the substrate in an etch chamber,

5 depositing a layer of titanium in a first deposition chamber, and

 depositing a layer of titanium nitride in a second deposition chamber.